

Silicon NPN Power Transistors

2SC2578

DESCRIPTION

- With TO-3PN package
- Complementary to 2SA1104
- High Power Dissipation
- High Current Capability

APPLICATIONS

- Audio power amplifier
- DC TO DC Converter

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

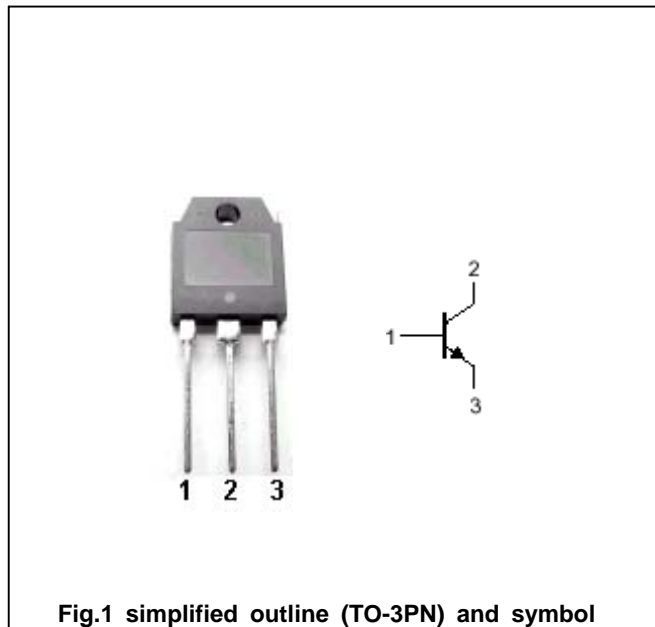


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	140	V
V_{CEO}	Collector-emitter voltage	Open base	100	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		7	A
P_C	Collector power dissipation	$T_C=25$	70	W
T_j	Junction temperature		150	
T_{stg}	Storage temperature		-55~150	

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =5mA; I _E =0	140			V
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA; R _{BE} =	100			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _C =0; I _E =5mA	6			V
I _{CBO}	Collector cut-off current	V _{CB} =100V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =4V; I _C =0			0.1	mA
h _{FE1}	DC current gain	I _C =1A; V _{CE} =5V	55		160	
h _{FE2}	DC current gain	I _C =3A; V _{CE} =5V	50			
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =3A; I _B =0.3A			2	V

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PACKAGE OUTLINE

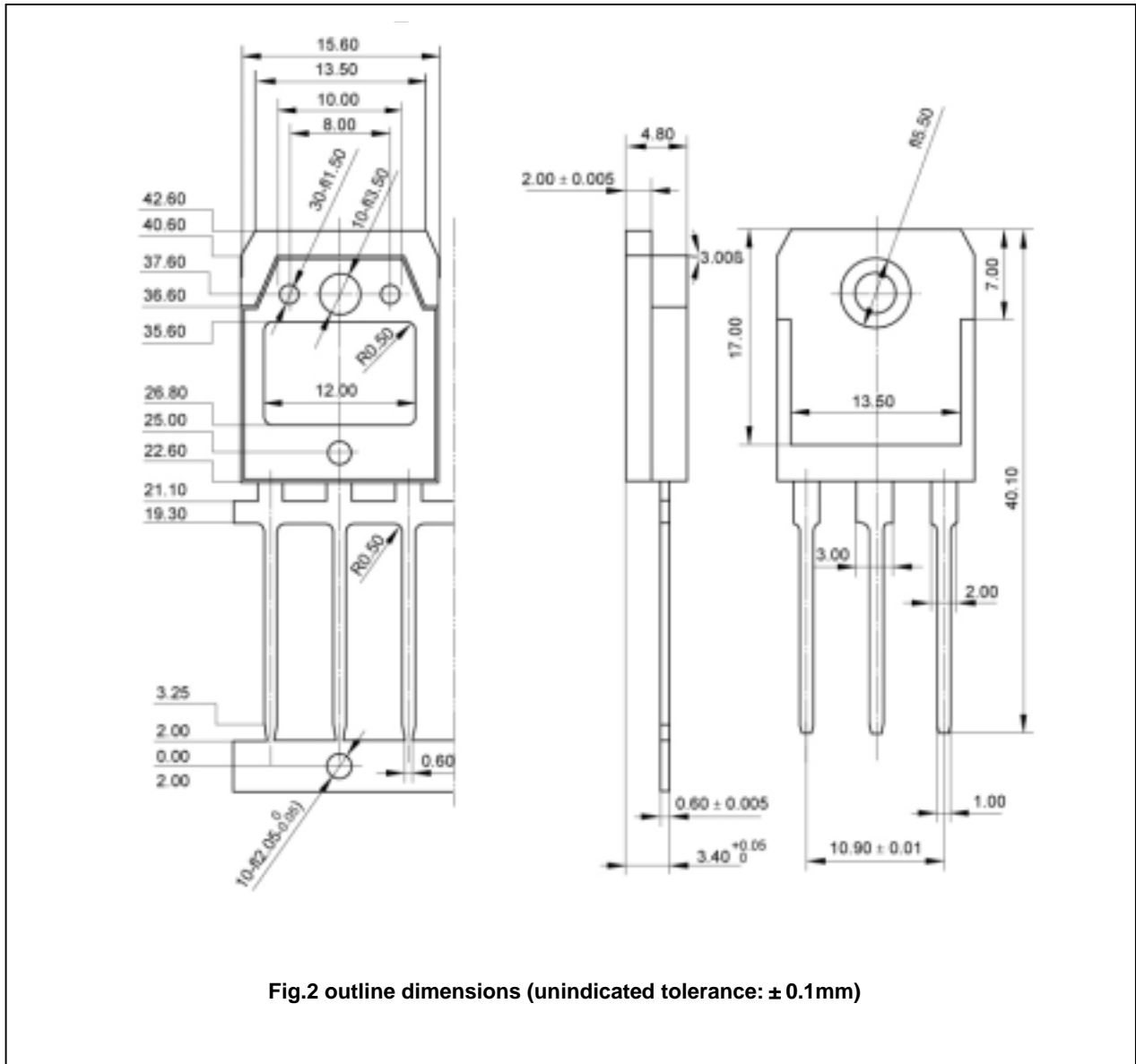


Fig.2 outline dimensions (unindicated tolerance: ± 0.1mm)